Form PTO-1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

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ATTY. DOCKET NO.	SERIAL NO.
M122-1531	09/755,673
APPLICANT: Leonard Forbes et al.	
FILING DATE: January 5, 2001	GROUP: 2823

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
K.N.	AA	5,605,857	02/97	Jost et al	437	760	Feb. 22, 1995
K.N.	AB	5,985,731	11/99	Weng et al	438	396	Aug. 17, 1998
K.N.	AC	6,395,650	05/02	Callegari et al	438	785	Oct. 23, 2000
	AD						
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	AF						
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
	AM							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER: Khuong Nguyen

DATE CONSIDERED: 12/10/04

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		Document Number	Date	Country	Class	Subclass	Translation Yes	Translation No
K.N.	AM	JP200058777A	02/00	Japan - electronic translation and abstract			X	
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	AO							
	AP							
	AQ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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Form PTO-1449 — U.S. DEPARTMENT OF COMMERCE — PATENT-AND-TRADEMARK-OFFICE

ATTY. DOCKET NO.	SERIAL NO.
MI22-1531	Filed Herewith
APPLICANT: Micron Technology, Inc.	
FILING DATE: Filed Herewith	GROUP: 2823

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K.N.	AC		Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S. ; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992
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Khiemnguyen	08/16/02

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MI22:1531	09/[illegible],673
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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-1531	SERIAL NO. Filed Herewith 09/755,613
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Micron Technology, Inc.	
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K.N.	AD		Changes in optical transmittance and surface morphology of AlN thin films exposed to atmosphere; Yoshihisa Watanabe, Yoshifumi Sakuragi, Yoshiki Amamoto, and Yoshikazu Nakamura; J. Mater. Res., Vol 13, No. 10, Oct. 1998; 1998 Materials Research Society; pp. 2956-61
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	AH		Nitrogen plasma source ion implantation for corrosion protection of aluminum 6061-T4; J. H. Booske, L. Zhang, W. Wang, K. Mente, N. Zjaba, C. Baum, and J.L. Shohet; J. Mater. Res. Vol. 12, No. 5, May 1997; 1997 Materials Research Society; pp. 1356-66
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